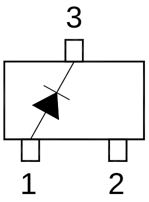
SB420D

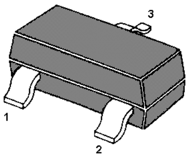
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for low power rectification

Features

- Small surface mounting type.
- High reliability.





SOT-23 Plastic Package

Marking

Marking Code: **FF**

Absolute Maximum Ratings (T_a= 25°C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	40	V
DC Reverse Voltage	V_R	40	V
Mean Rectifying Current	I_O	0.1	A
Peak Forward Surge Current [1]	I_{FSM}	1	A
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-40 to +125	°C

[1] 60Hz for 1 ∿

Characteristics at T_a = 25 °C

Parameter	Symbol	Min	Typ	Max	Unit
Forward Voltage at I_F = 10mA	V_F	-	-	0.45	V
Reverse Current at V_R =10V	I_R	-	-	1	µA
Capacitance Between Terminals at V_R =10V, f=1MHz	C_T	-	6	-	pF

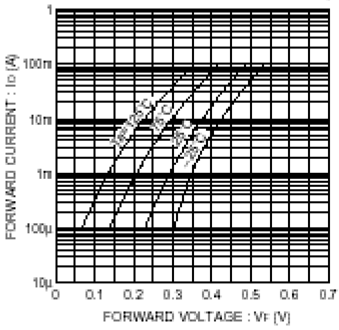


Fig.1 Forward characteristics

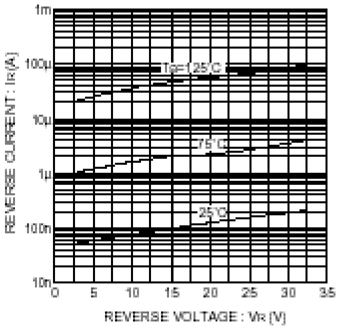


Fig.2 Reverse characteristics

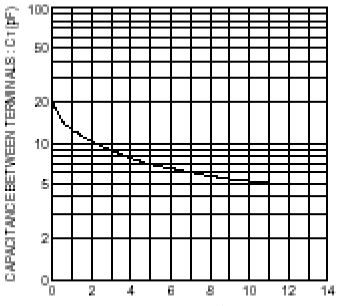


Fig.3 Capacitance between terminals characteristics

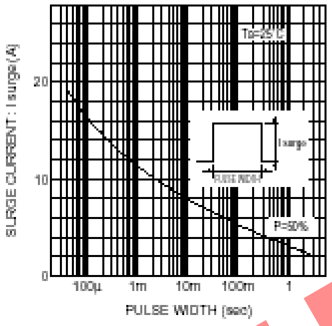


Fig.4 Surge current characteristics

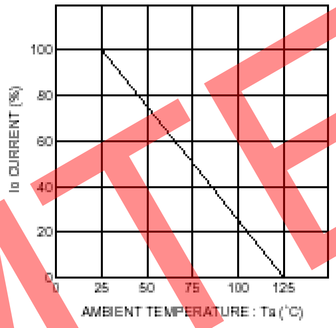


Fig.5 Derating curve
(mounting on glass epoxy PCBs)